

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
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242189US2SSERIAL NO. 10/650671  
NEW APPLICATION

## LIST OF REFERENCES CITED BY APPLICANT

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
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	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

VIN	AW	Roy SCHEUERLEIN, et al., "A10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell" IEEE International Solid State Circuits Conference(ISSCC) Digest of Technical Papers, pp. 128-129, February 8, 2000				
VIN	AX	M. Durlam, et al., " Nonvolatile RAM based on Magnetic Tunnel Junction Elements", IEEE International Solid-State Circuits Conference, (ISSCC) Digest of Technical Papers, pp. 130-131, February 8, 2000				
VIN	AY	Peter K. Naji, et al., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM", IEEE International Solid-State Circuits Conference (ISSCC) Digest of Technical Papers, pp. 122-123, February 6, 2001				
	AZ				<input type="checkbox"/> Additional References sheet(s) attached	

Examiner

*W. Huel*

Date Considered

9/7/04

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.